

October 2013

FQPF19N10

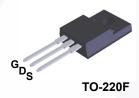
N-Channel QFET® MOSFET 100 V, 13.6 A, 100 m Ω

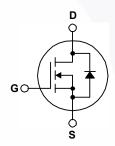
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 13.6 A, 100 V, $R_{DS(on)}$ =100 m $\Omega(Max.)$ @ V_{GS} =10 V, I_D =6.8 A
- Low Gate Charge (Typ. 19 nC)
- Low Crss (Typ. 32 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

| Symbol | Parameter | | FQPF19N10 | Unit |
|-----------------------------------|---|----------|-------------|------|
| V _{DSS} | Drain-Source Voltage | | 100 | V |
| I _D | Drain Current - Continuous (T _C = 25° | °C) | 13.6 | А |
| | - Continuous (T _C = 100 | O°C) | 9.6 | А |
| I _{DM} | Drain Current - Pulsed | (Note 1) | 54.4 | A |
| V _{GSS} | Gate-Source Voltage | | ± 25 | V |
| E _{AS} | Single Pulsed Avalanche Energy | (Note 2) | 220 | mJ |
| I _{AR} | Avalanche Current | (Note 1) | 13.6 | Α |
| E _{AR} | Repetitive Avalanche Energy | (Note 1) | 3.8 | mJ |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | 6.0 | V/ns |
| P_{D} | Power Dissipation (T _C = 25°C) | | 38 | W |
| | - Derate above 25°C | | 0.25 | W/°C |
| T _J , T _{STG} | Operating and Storage Temperature Ra | nge | -55 to +175 | °C |
| T _L | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | | 300 | °C |

Thermal Characteristics

| Symbol | Parameter | FQPF19N10 | Unit |
|-----------------|---|-----------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max. | 3.95 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Max. | 62.5 | °C/W |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|-----------|-----------------|-----------|------------|----------|
| FQPF19N10 | FQPF19N10 | 19N10 TO-220F - | | - | 50 |

Electrical Characteristics

T_C = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Unit | |
|------------------------------------|--|--|-----|-----|------|------|--|
| Off Cha | Off Characteristics | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 100 | | | V | |
| ΔBV_{DSS} / ΔT_{J} | Breakdown Voltage Temperature Coefficient | I _D = 250 μA, Referenced to 25°C | | 0.1 | | V/°C | |
| I _{DSS} | Zara Cata Valtaga Drain Current | V _{DS} = 100 V, V _{GS} = 0 V | | | 1 | μΑ | |
| | Zero Gate Voltage Drain Current | V _{DS} = 80 V, T _C = 150°C | | | 10 | μΑ | |
| I _{GSSF} | Gate-Body Leakage Current, Forward | V _{GS} = 25 V, V _{DS} = 0 V | | | 100 | nA | |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | V _{GS} = -25 V, V _{DS} = 0 V | | | -100 | nA | |
| | | | | | | | |
| On Cha | On Characteristics | | | | | | |

| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | 2.0 | | 4.0 | V |
|---------------------|--------------------------------------|--|-----|-------|-----|---|
| R _{DS(on)} | Static Drain-Source On-Resistance | $V_{GS} = 10 \text{ V}, I_D = 6.8 \text{ A}$ | | 0.078 | 0.1 | Ω |
| 9 _{FS} | Forward Transconductance | $V_{DS} = 40 \text{ V}, I_{D} = 6.8 \text{ A}$ | \ | 10 | | S |

Dynamic Characteristics

| C _{iss} | Input Capacitance | $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ | 600 | 780 | pF |
|------------------|------------------------------|--|---------|-----|----|
| Coss | Output Capacitance | f = 1.0 MHz | 165 | 215 | pF |
| C _{rss} | Reverse Transfer Capacitance | | 32 | 40 | pF |

Switching Characteristics

| | _ | | | | | |
|---------------------|---------------------|--|-----------|-----|-----|----|
| t _{d(on)} | Turn-On Delay Time | $V_{DD} = 50 \text{ V}, I_{D} = 19 \text{ A},$ | | 7.5 | 25 | ns |
| t _r | Turn-On Rise Time | $R_G = 25 \Omega$ | | 150 | 310 | ns |
| t _{d(off)} | Turn-Off Delay Time | G | | 20 | 50 | ns |
| t _f | Turn-Off Fall Time | (Note 4) | / | 65 | 140 | ns |
| Q_g | Total Gate Charge | V _{DS} = 80 V, I _D = 19 A, | | 19 | 25 | nC |
| Q _{gs} | Gate-Source Charge | V _{GS} = 10 V | / | 3.9 | | nC |
| Q _{gd} | Gate-Drain Charge | (Note 4) | | 9.0 | | nC |

Drain-Source Diode Characteristics and Maximum Ratings

| IS | Maximum Continuous Drain-Source Diode Forward Current | | | 13.6 | Α |
|-----------------|---|--|-------------|------|----|
| I _{SM} | Maximum Pulsed Drain-Source Diode Forward Current | | | 54.4 | Α |
| V _{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0 V, I _S = 13.6 A | | 1.5 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _S = 19 A, | 78 | | ns |
| Q _{rr} | Reverse Recovery Charge | $dI_{F} / dt = 100 A/\mu s$ | 200 | | nC |

- **Notes:**1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 1.8mH, $|_{AS}$ = 13.6A, V_{DD} = 25V, R_{G} = 25 Ω , Starting T_{J} = 25°C 3. $|_{SD}$ ≤ 19A, di/dt ≤ 300A/ μ s, V_{DD} ≤ BV $_{DSS}$, Starting T_{J} = 25°C 4.Essentially independent of operating temperature

Typical Characteristics

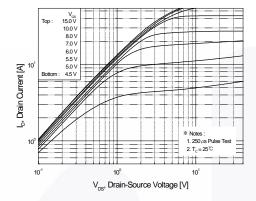


Figure 1. On-Region Characteristics

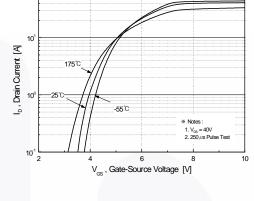


Figure 2. Transfer Characteristics

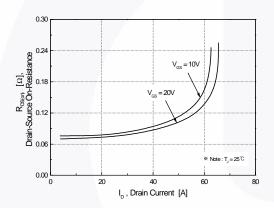


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

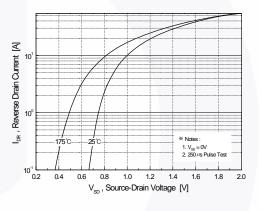


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

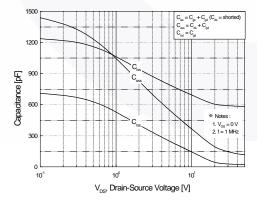


Figure 5. Capacitance Characteristics

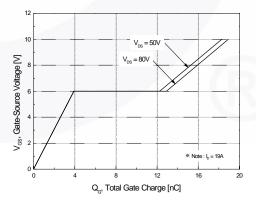


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

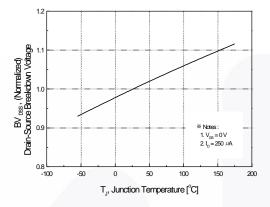
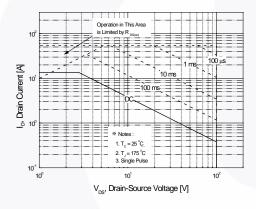


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



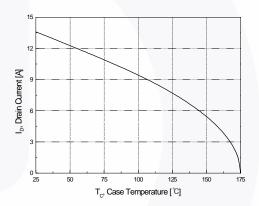


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

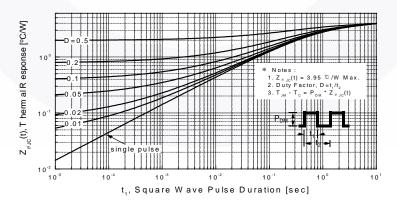


Figure 11. Transient Thermal Response Curve

Figure 12. Gate Charge Test Circuit & Waveform

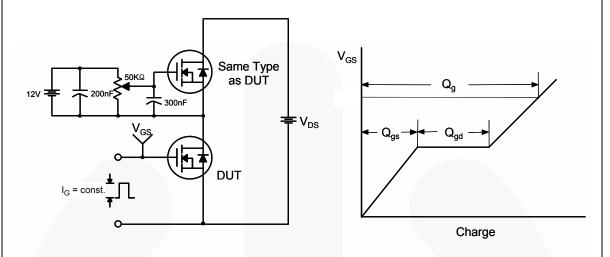


Figure 13. Resistive Switching Test Circuit & Waveforms

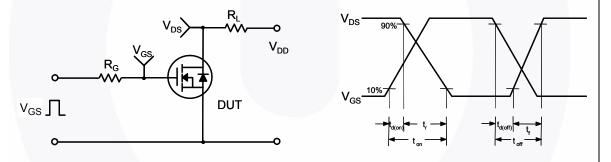
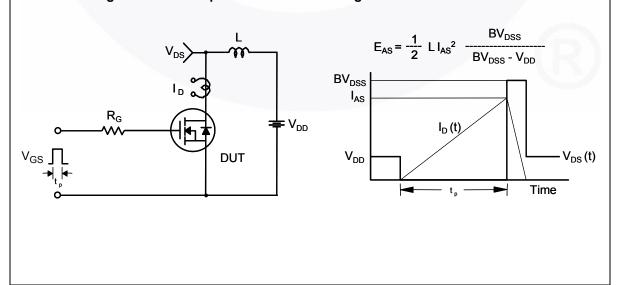
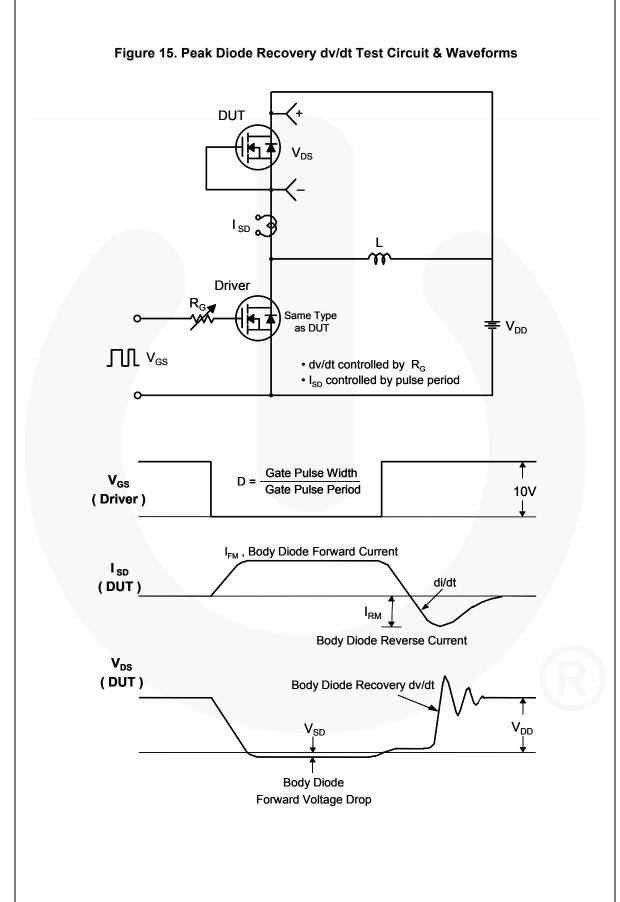


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





Mechanical Dimensions

TO-220F 3L

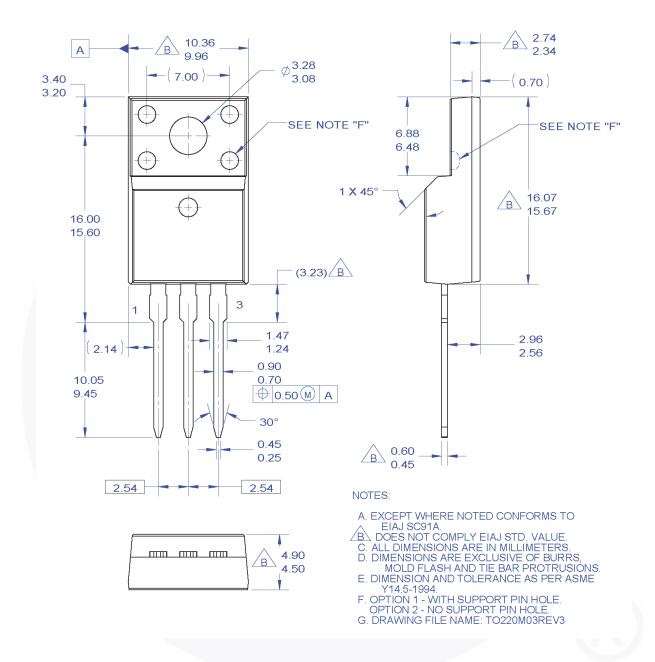


Figure 16. TO220, Molded, 3LD, Full Pack, EIAJ SC91, Straight Lead

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Dimension in Millimeters





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